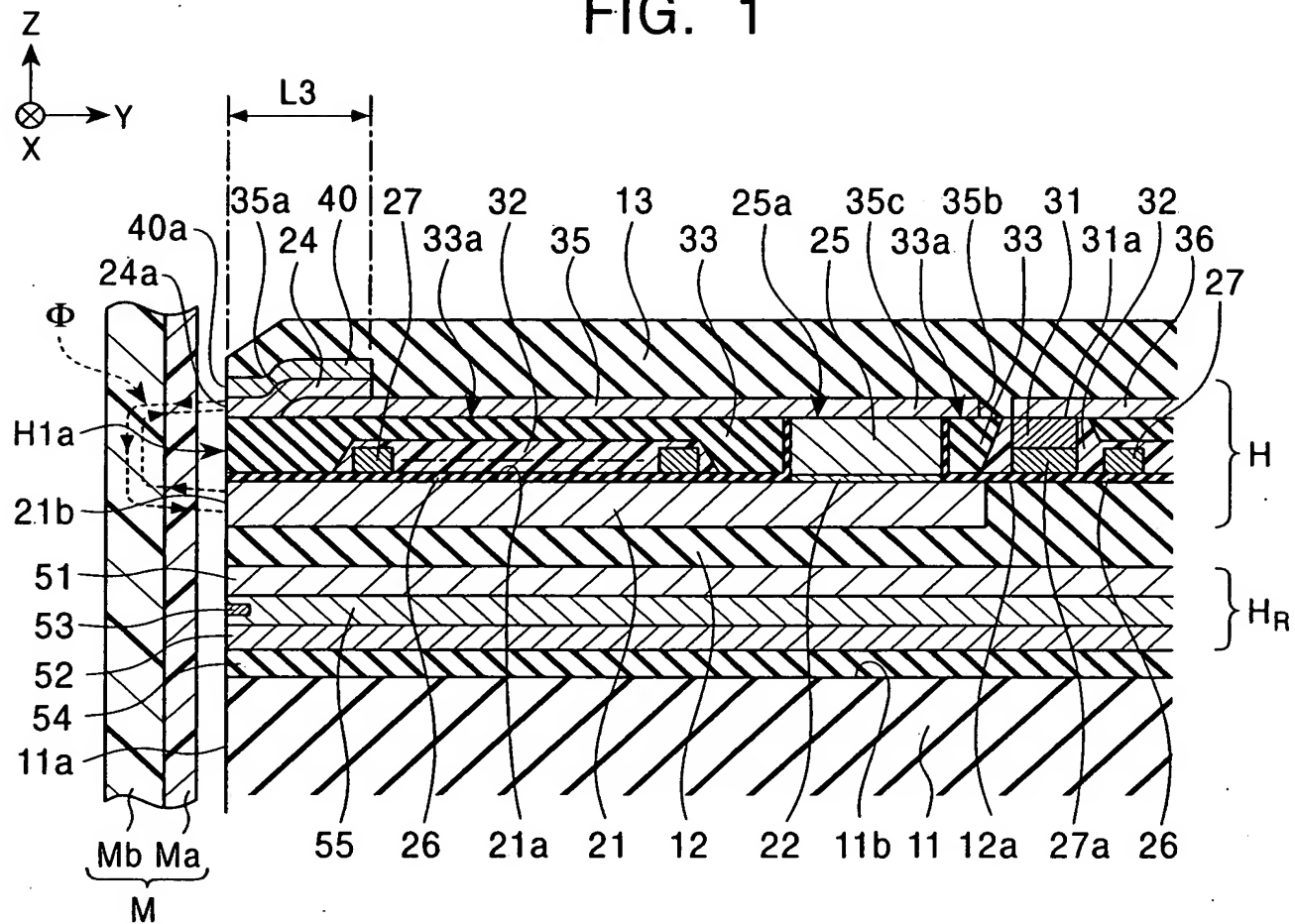
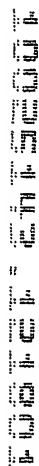


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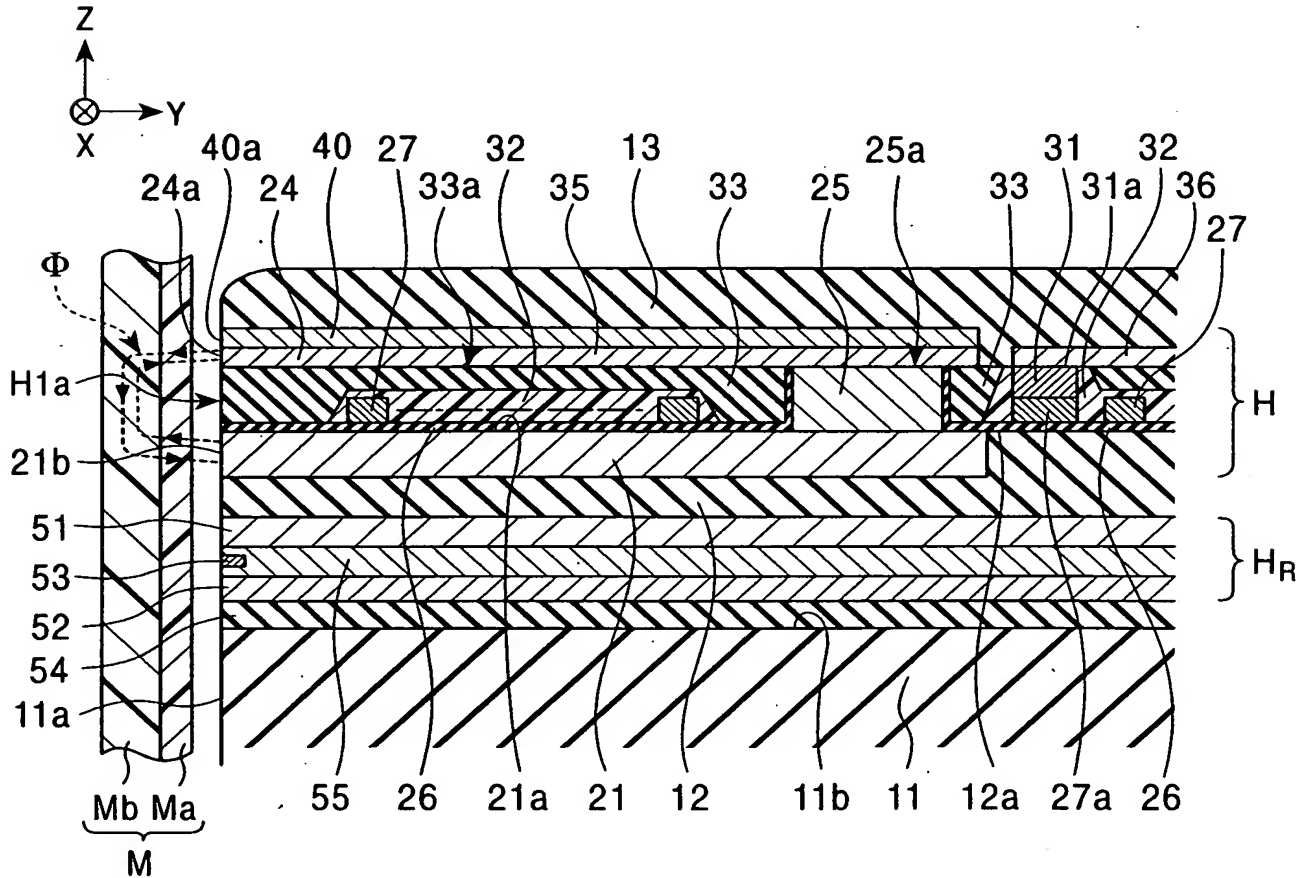
FIG. 1





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FIG. 3



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FIG. 4

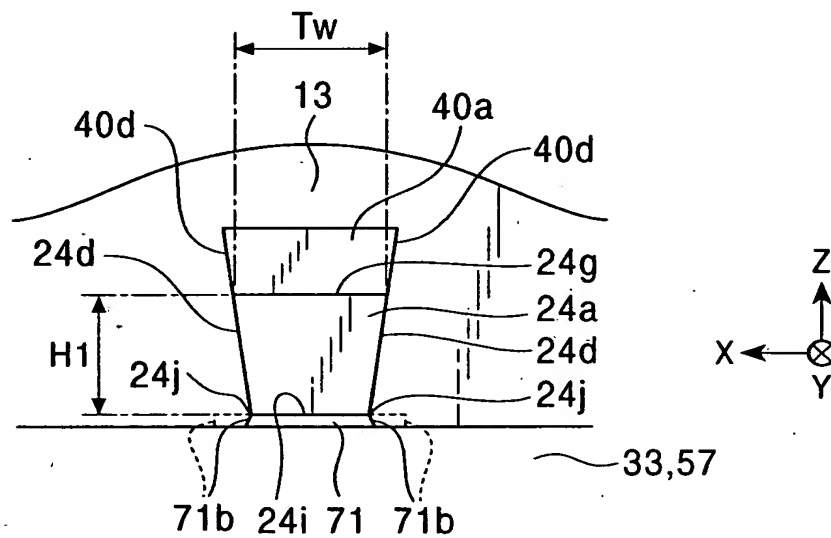
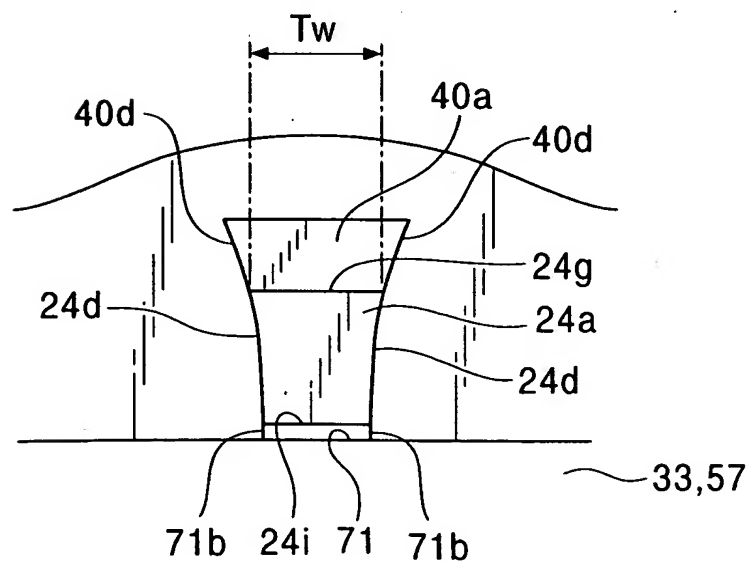


FIG. 5



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FIG. 6

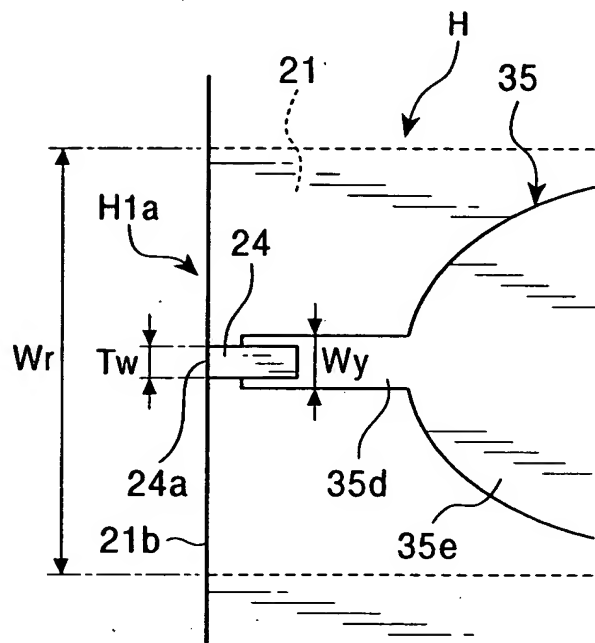
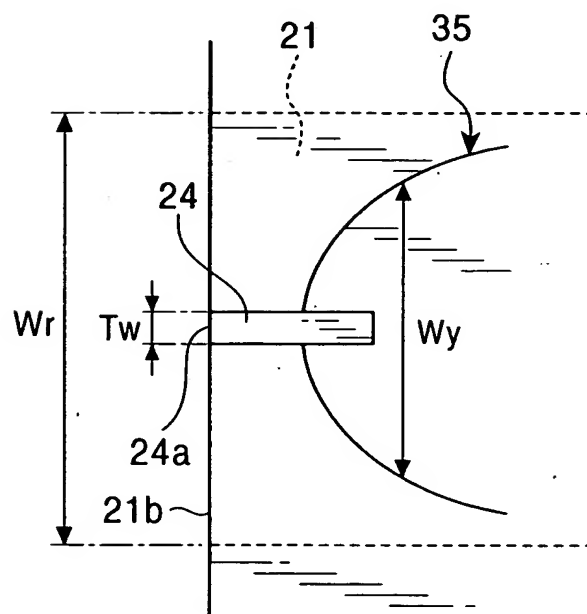


FIG. 7



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FIG. 8

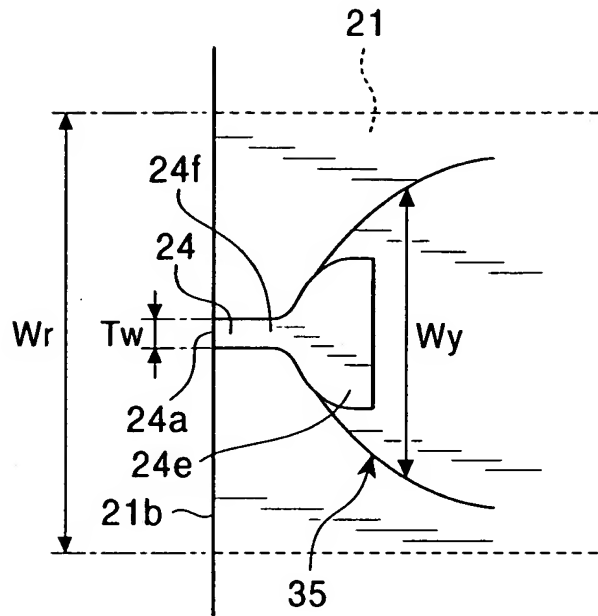
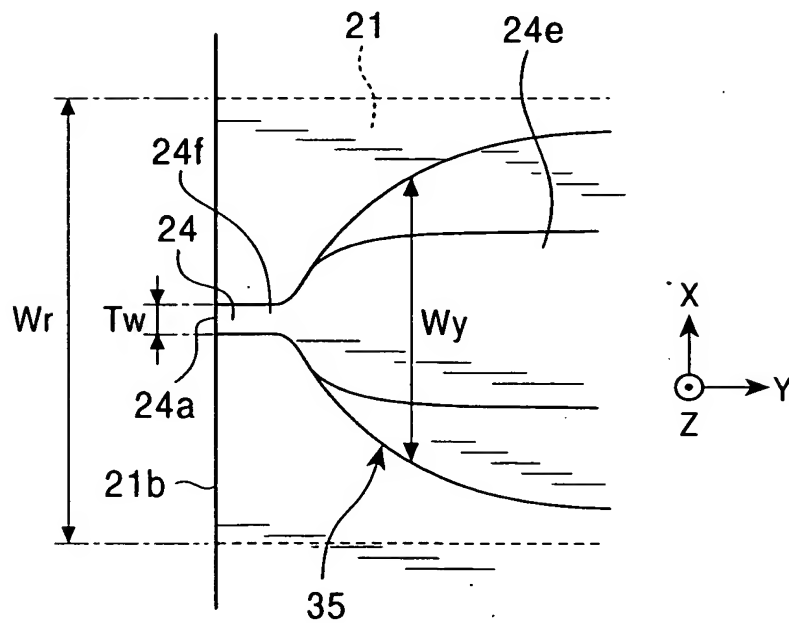


FIG. 9



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FIG. 10

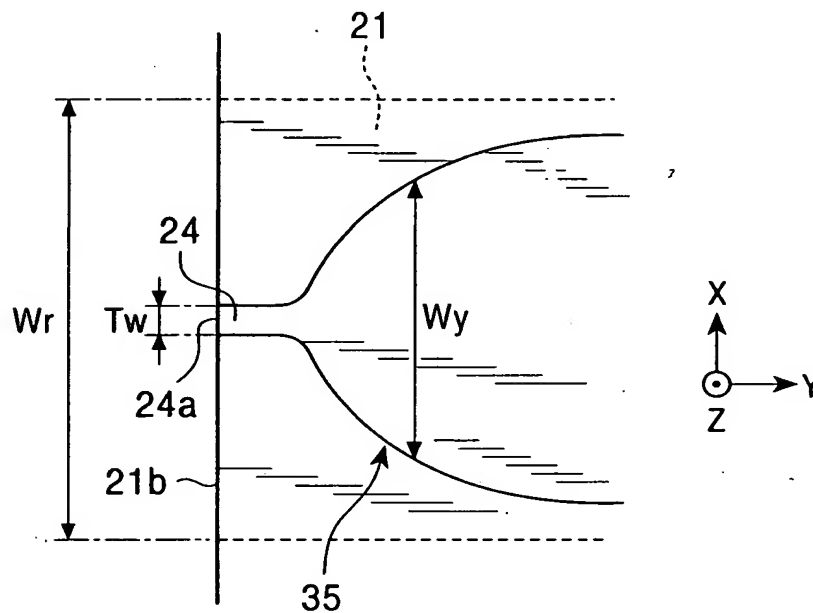
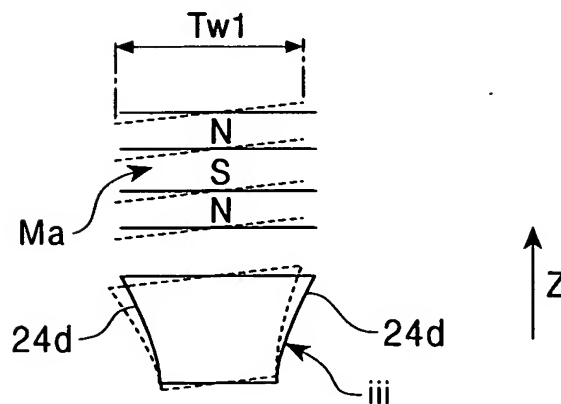


FIG. 11



A cross-sectional view of a semiconductor device. The device consists of a substrate 12, a first conductive layer 21, a second conductive layer 26, and a third conductive layer 25. The substrate 12 is the bottom layer, followed by the first conductive layer 21, then the second conductive layer 26, and finally the third conductive layer 25 on top. The third conductive layer 25 is a rectangular block. A coordinate system (X, Y, Z) is shown on the right, with Z pointing up, Y pointing right, and X pointing out of the page (indicated by a circle with a cross).

[illegible]

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FIG. 15

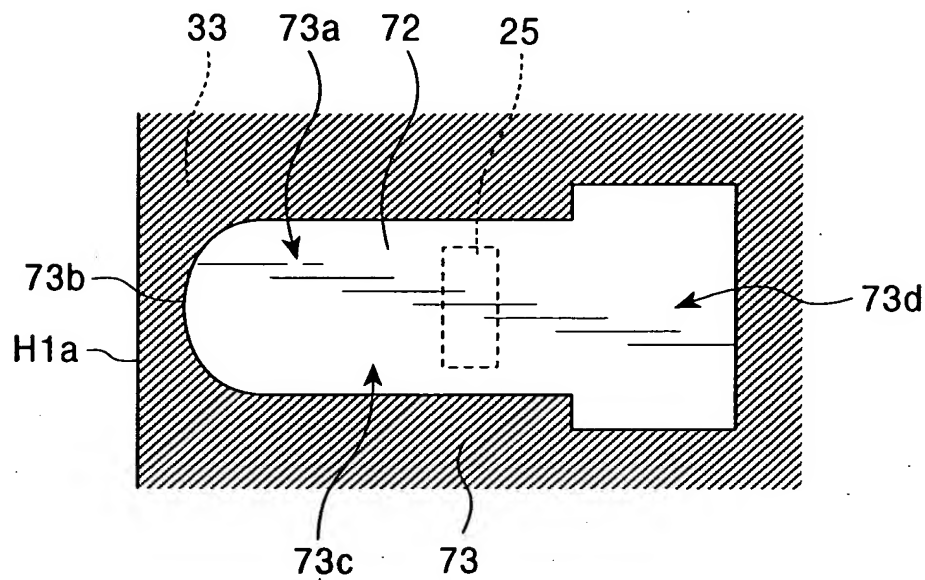
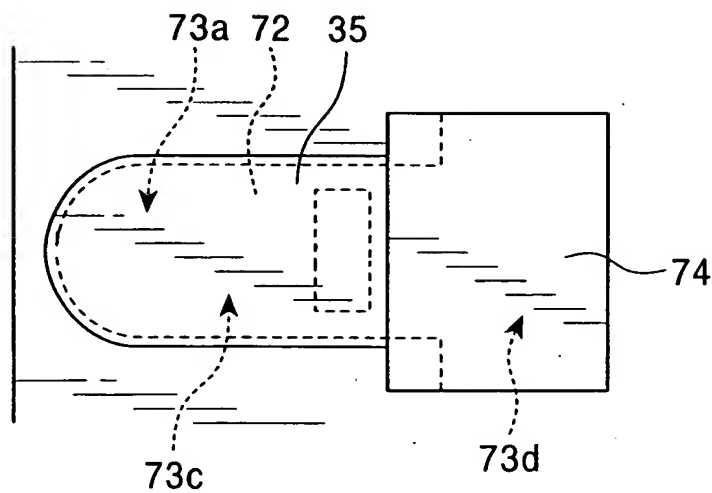


FIG. 16



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FIG. 17

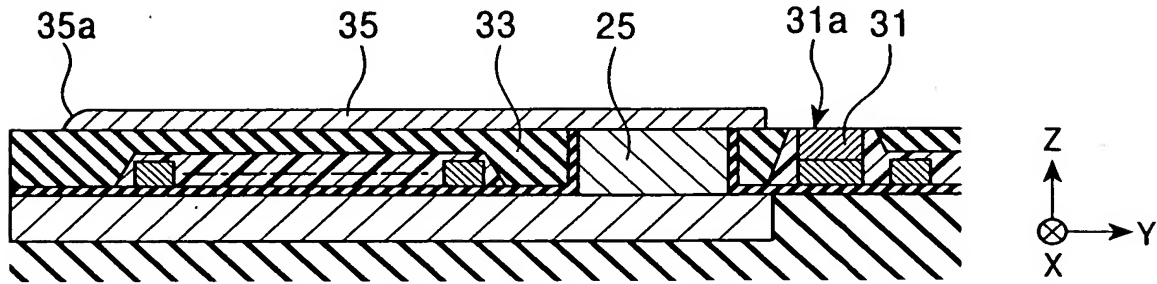
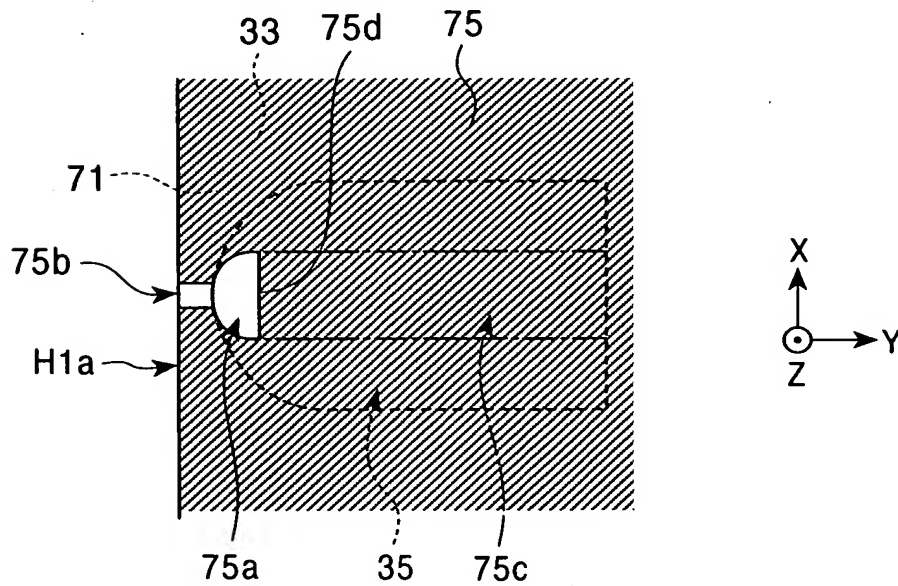


FIG. 18



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FIG. 19

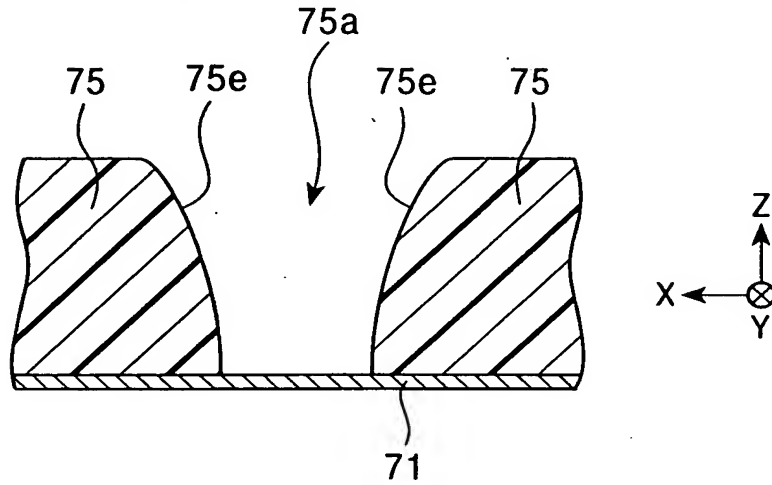
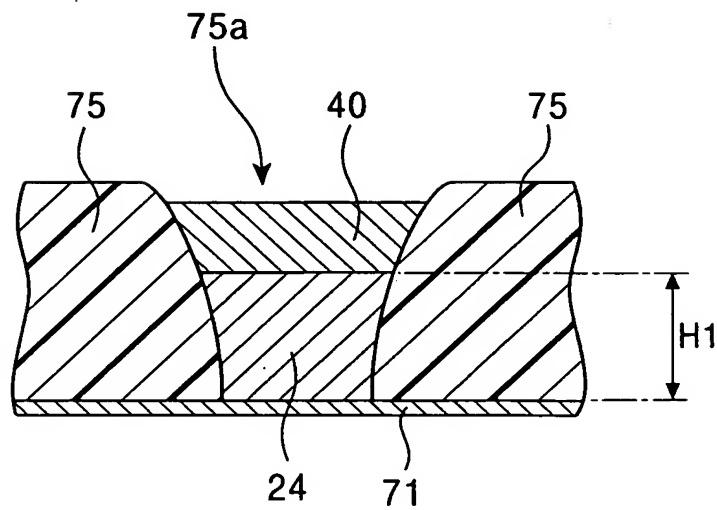


FIG. 20



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FIG. 21

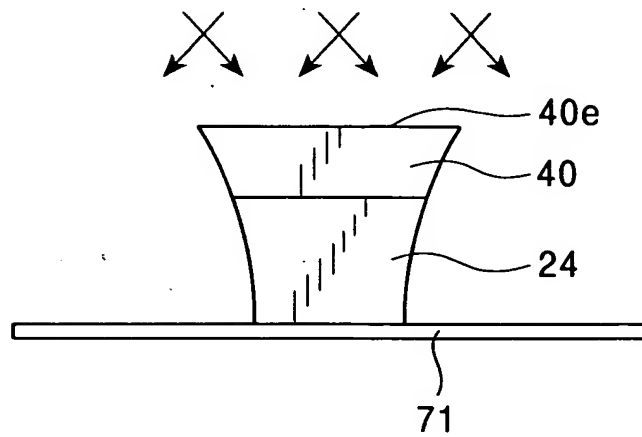
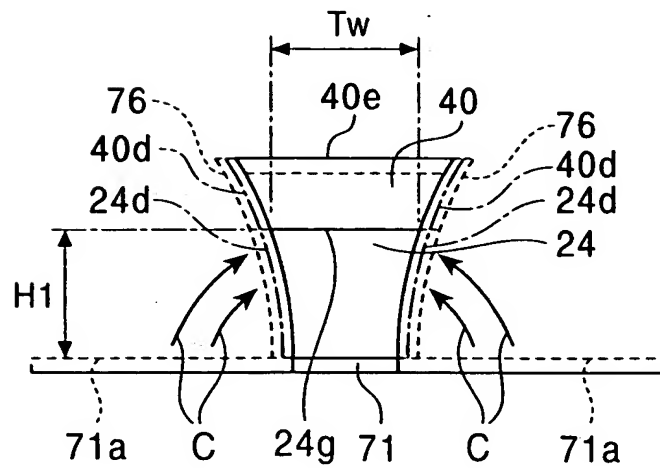


FIG. 22



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FIG. 23

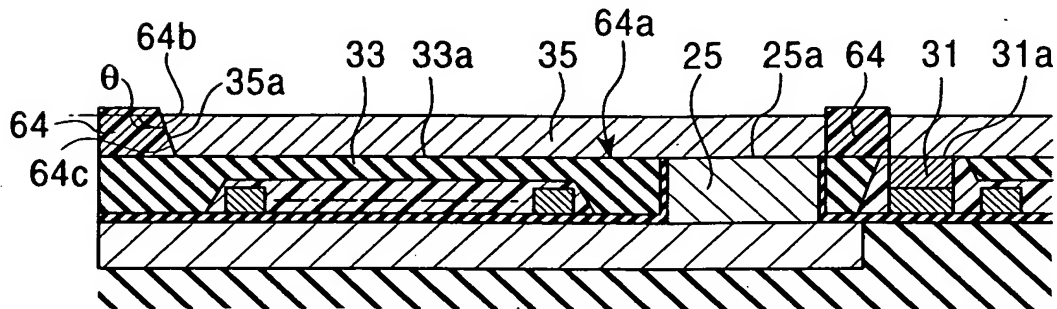


FIG. 24

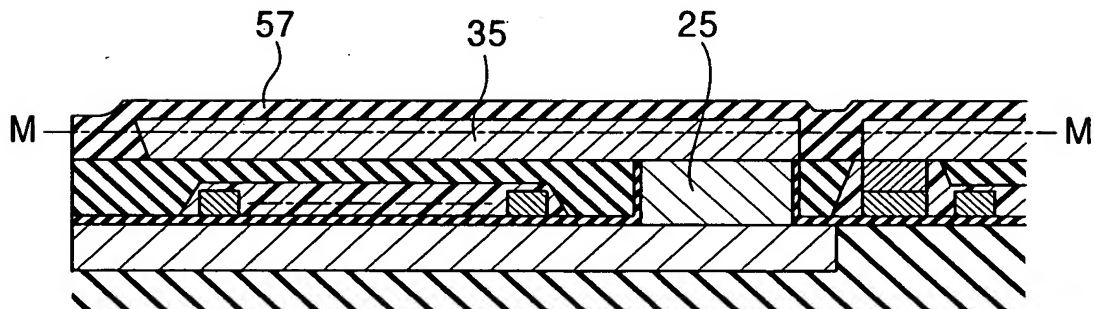
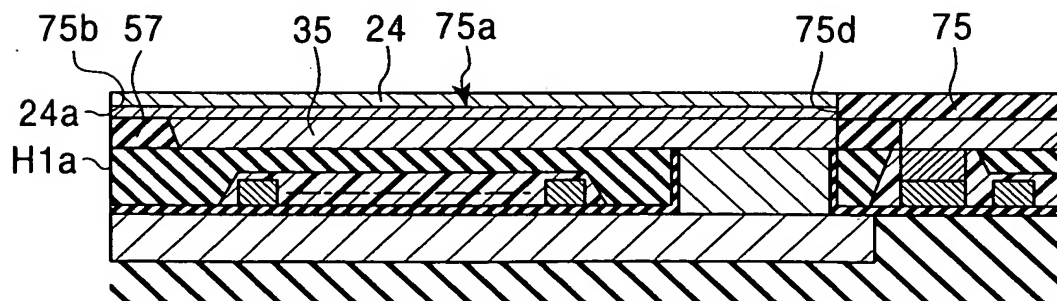
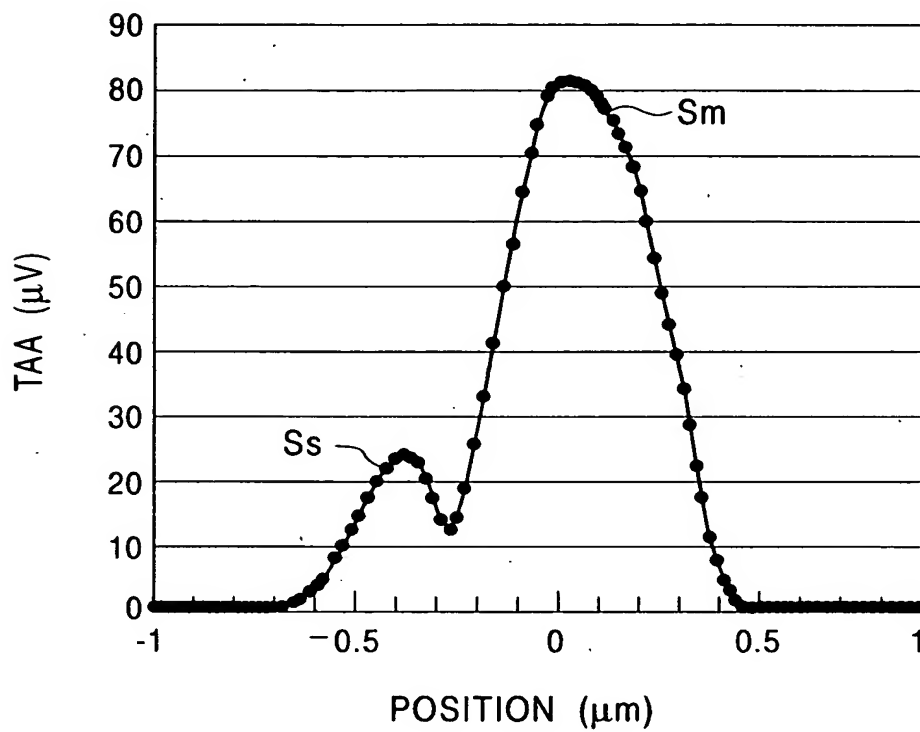


FIG. 25



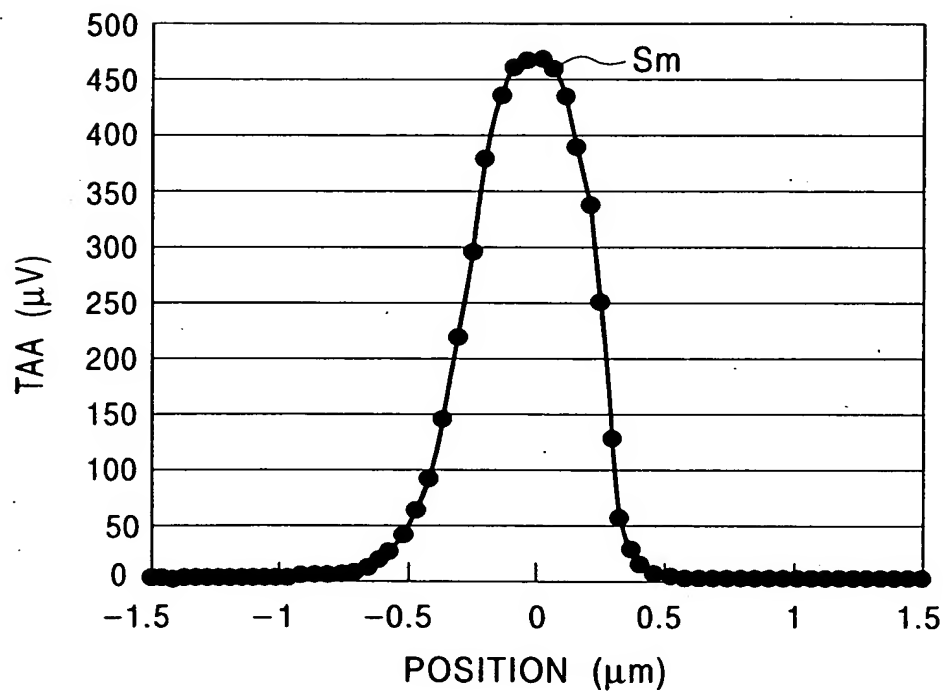
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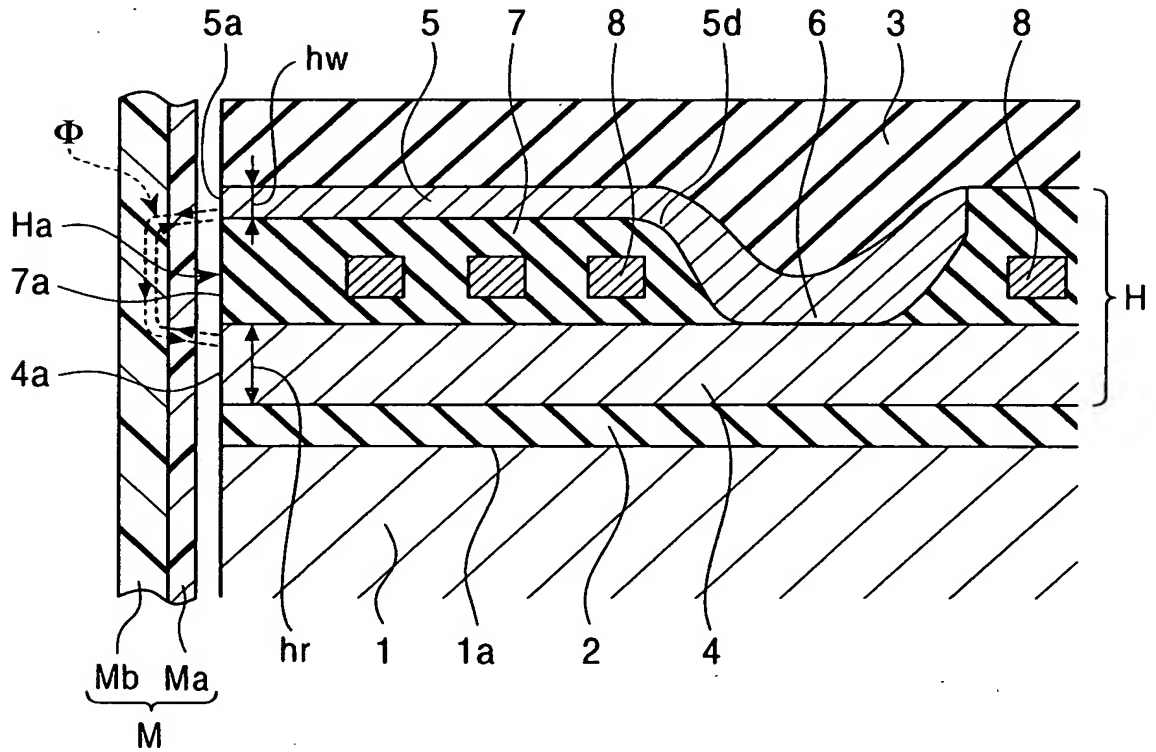
FIG. 26



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FIG. 27





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FIG. 29
PRIOR ART

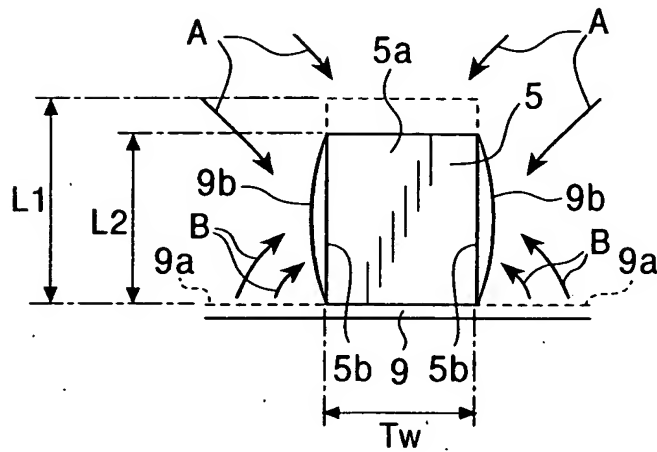


FIG. 30
PRIOR ART

